

Controlled Si-Drift Detectors



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Int'l Symposium on Detector Development, April 3-6, 2006, Stanford Linear Accelerator Center, USA



Position-sensing with classical Silicon Drift Detectors



Wafer: 5", (NTD) silicon, 3 k Ω ·cm resistivity, 300 μ m thickness Active area: 7.02 × 7.53 cm²

~5 Mpixel with ~500 output channels !



Wafer: 4" silicon, 300 μm thickness Active area: 55 cm² (4.2cm radius)

...but... > START TRIGGER NEEDED ! no imaging of random sources (x/g/...) !

FREE LATERAL BROADENING !

- \rightarrow doping inhomogeneities
- → limited spectroscopic performance
- \rightarrow reduction of the event rate





A.Castoldi, C.Guazzoni, IEEE TED, 46, 2 (1999) A.Castoldi, E.Gatti, C.Guazzoni, A.Longoni, P.Rehak, L.Strüder, NIM A439 (2000)



Novel features

- potential minimum near top surface
 - suppressed lateral broadening
- control of drift field: "integrate-readout" mode
- integrated front-end JFET: high energy/position resol.
 - fast timing signal from back electrodes

• electron packets are drifted at high speed (0.5-1.5 cm/µs) towards point-like anodes (<100 fF)

- deposited energy is obtained from the electron charge (Q)
- interaction position along the drift is obtained from the drift time (T_d)
- interaction position along 2nd coordinate is obtained by anode segmentation

P <u>fast readout, position sensing/reduced no. of channels</u> and <u>spectroscopy</u> of radiation



CDD working principle: simulation @ z=12 µm





Controlled-Drift Detector - Layout and photo

A.Castoldi, A.Galimberti, C.Guazzoni, P.Rehak, L.Strüder, NIM A512, October 2003

0.3 cm² active area - pixel 120μ m/180 μ m



High energy implantation (20 MeV) instead of grown epitaxy ☆ drift channel is located at about 7 **m**m from the implanted surface

Designed, layouted and tested at Politecnico di Milano-INFN, Italy Produced at the Halbleiterlabor of the Max Planck Institut, Munich (D) Detail of anode region with integrated front-end JFETs



Mounted 6x6 mm² prototype









energy [keV]

"Electronic" collimation

A.Castoldi, G.Cattaneo, A.Galimberti, C.Guazzoni, P.Rehak, L.Strüder, IEEE TNS 49 (3), June 2002





2-D spectroscopic imaging of X-rays with CDDs

Exp. CODERA (2003) - INFN - Sezione di Milano - Gruppo V

A.Castoldi, G. Cattaneo, A.Galimberti, C.Guazzoni, P.Rehak, L.Strüder, IEEE TNS 49, 3 (2002) A.Castoldi, A.Galimberti, C.Guazzoni, P.Rehak, L.Strüder, NIM A512 (2003)

Radiographic image of a lizard*...

pixel 120mm, 10⁵ frame/s, 15 keV x-rays, T=300K



Sincrotrone Trieste – SYRMEP beam line



... and spectroscopic analysis of each pixel







2D/3D tomographic imaging at 100 kHz frame rate

A. Castoldi, A. Galimberti, C. Guazzoni, L.Strüder, "New Silicon Drift Detectors for Synchrotron Radiation Applications", Nuclear Science Symposium Conference Record, 2004 IEEE, 16-22 Ottobre 2004, Roma, Italia.

pixel 120mm, 28 keV x-rays (0.44 Å), 10⁵ frame/s, T=300K





Iano



2D Elemental mapping by K-edge subtraction imaging

K-edge subtraction imaging (dual energy technique)



The distribution of a known element (i.e. silver) in the sample is obtained by imaging the sample in two X ray windows, one below and the other above the K-edge of silver, and looking at the image difference.

The spectroscopic capability of the CDD allows mapping of principal elements in the sample with ~100µm position resolution from a <u>single image acquisition</u> (i.e. multiple-energy technique)

Exp. CODERA - Gr. V - INFN Sez. Milano A.Castoldi, A.Galimberti, C.Guazzoni, P.Rehak, L.Strüder, R.Menk, NIM. A510 (2003) 57-62.

Multi-element sample (Ag, In, etc.)



DE (*Ag*) = (26.7 keV-24 keV)



Ag distribution

In distribution

DE (*In*)=(29.1 keV-26.7 keV)





Diffraction Enhanced Breast Imaging (DEBI)





Experimental results on tissue: contrast and specificity





6 mm







E=18 keV

c ÷E



Time-resolved X-ray imaging of repetitive processes

Experimental setup: CDD operated at 100 kHz drift field 400 V/cm, T=300 K

Input signal: 219 Hz sine wave Mask displacement: 2.3 mm p-p

Acquired time-sliced X-ray images (integrate-readout, 100kHz)



1 µs resolution in free-running mode **pump-and-probe** techniques







A. Castoldi, A. Galimberti, C. Guazzoni, P.Rehak, R-Hartmann, L Strüder, A. H. Walenta, "Multi-linear Drift Detectors for X-ray and Comtpon Imaging", 10° European Symposium on Semiconductor Detectors, Wildbad-Kreuth, June 12-16 2005 (NIM)



Electron tracking of the *first* Compton scatter can significantly increase sensitivity of Compton telescopes:

Approximate determination of dE/dx from experimental data:

- direction of recoil electron

- data fitting: recoil electron energy, deposited energy, escape energy

- analysis of back signals may provide Depth-Of-Interaction information

Silicon CDD scatter detector





Scientific collaboration with MPI Munich for technology develop./detector production (2005)



Preliminary tests with Am-241 (march '06)

